







\*D1002

\*PSPICE MODEL FOR POINT NINE RF N-CHANNEL VERTICAL DMOS POWER FET

\*May 2004

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*          _____GATE
*          I   _____DRAIN
*          I   I   _____SOURCE
*          I   I   I
.SUBCKT D1002  10  20  30
*Cin1,Cin2 & Lin model the input side of the package
Cin1  10   30   0.31p
Lin   10   11   0.64n
Cin2  11   30   0.24p
LG    11   12   1n    ;Gate bond wire inductance
CGS   12   13   92p   ;Gate-source capacitance
MOS   14   12   13    13  D1002 L=0.9U W=0.112    ;D G S B LEVEL1
JFET  16   13   14    D1002                      ;D G S
DBODY 13   16   D1002                              ;P N
LS    13   30   0.7n  ;Source bond wire inductance
CGD   12   16   2p    ;Gate-drain feedback capacitance

*Cout1,Cout2 & Lout model the output side of the package
Cout1 16   30   0.65p
Lout   16   20   1.5n
Cout2 20   30   0.6p

.MODEL D1002 NMOS (VTO=4.76 KP=2.811E-5 LAMBDA=0.032 RD=0.038 RS=0.153)
.MODEL D1002 NJF (VTO=-4.3 BETA=0.5 LAMBDA=0.54)
.MODEL D1002 D (CJO=164.4P RS=0.25 VJ=0.7 M=0.35 BV=75)

.ENDS
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